

## **New Beam Test Results of 3D Pixel Detectors Constructed With Poly-Crystalline CVD Diamond**

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Toronto, ON, Canada

**Michael Reichmann on behalf of the RD42 Collaboration**

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- 5 Outlook

## Section 1

### Motivation

# Diamond as Detector Material

- innermost tracking layers  $\rightarrow$  highest radiation damage  $\mathcal{O}$  (GHz/cm<sup>2</sup>)
- current detectors is designed to survive  $\sim 12$  month in High-Luminosity LHC
- $\rightarrow$  **R&D for more radiation tolerant detector designs and/or materials**

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## Diamond as Detector Material:

- properties
  - ▶ radiation tolerant
  - ▶ isolating material
  - ▶ high charge carrier mobility
  - ▶ smaller signal than in silicon with same thickness (large bandgap)
  - ▶ after  $1 \cdot 10^{16}$  n/cm<sup>2</sup> the mean drift path in diamond larger than in silicon

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## Work of RD42:

- investigate signals and radiation tolerance in various detector designs:
  - ▶ Pad Detectors  $\rightarrow$  whole diamond as single cell readout
  - ▶ Pixel Detectors  $\rightarrow$  diamond sensor on pixel readout chip
  - ▶ 3D Pixel Detectors  $\rightarrow$  3D diamond detector on pixel readout chip

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  - ▶ Pad Detectors
  - ▶ Pixel Detectors
  - ▶ 3D Pixel Detectors  $\rightarrow$  this talk

## RD42 Collaboration

A. Alexopoulos<sup>3</sup>, M. Artuso<sup>20</sup>,  
 F. Bachmair<sup>24</sup>, L. Băni<sup>24</sup>, M. Bartosik<sup>3</sup>, J. Beacham<sup>13</sup>, H. Beck<sup>23</sup>,  
 V. Bellini<sup>2</sup>, V. Belyaev<sup>12</sup>, B. Bentele<sup>19</sup>, A. Bes<sup>27</sup>, J.-M. Brom<sup>7</sup>,  
 M. Bruzzi<sup>4</sup>, G. Chiodini<sup>26</sup>, D. Chren<sup>18</sup>, V. Cindro<sup>9</sup>, G. Claus<sup>7</sup>,  
 J. Collot<sup>27</sup>, J. Cumalat<sup>19</sup>, A. Dabrowski<sup>3</sup>, R. D'Alessandro<sup>4</sup>,  
 D. Dauvergne<sup>27</sup>, W. de Boer<sup>10</sup>, S. Dick<sup>13</sup>, C. Dorfer<sup>24</sup>,  
 M. Dünser<sup>3</sup>, G. Eigen<sup>30</sup>, V. Eremin<sup>6</sup>, G.T. Forcolin<sup>22</sup>,  
 J. Forneris<sup>15</sup>, L. Gallin-Martel<sup>27</sup>, M.L. Gallin-Martel<sup>27</sup>,  
 K.K. Gan<sup>13</sup>, M. Gastal<sup>3</sup>, C. Giroletti<sup>17</sup>, M. Goffe<sup>7</sup>, J. Goldstein<sup>17</sup>,  
 A. Golubev<sup>3</sup>, A. Gorišek<sup>9</sup>, E. Grigoriev<sup>8</sup>, J. Grosse-Knetter<sup>23</sup>,  
 A. Grummer<sup>21</sup>, B. Gui<sup>13</sup>, M. Guthoff<sup>3</sup>, B. Hiti<sup>9</sup>, D. Hits<sup>24</sup>,  
 M. Hoferkamp<sup>21</sup>, T. Hofmann<sup>3</sup>, J. Hosselet<sup>7</sup>, J.-Y. Hostachy<sup>27</sup>,  
 F. Hügging<sup>1</sup>, C. Hutton<sup>17</sup>, J. Janssen<sup>1</sup>, H. Kagan<sup>13</sup>,  
 K. Kanxheri<sup>28</sup>, G. Kasieczka<sup>24</sup>, R. Kass<sup>13</sup>, M. Kis<sup>5</sup>,  
 G. Kramberger<sup>9</sup>, S. Kuleshov<sup>8</sup>, A. Lacoste<sup>27</sup>, S. Lagomarsino<sup>4</sup>,  
 A. Lo Giudice<sup>15</sup>, I. López Paz<sup>22</sup>, E. Lukosi<sup>25</sup>, M. Maazouzi<sup>7</sup>,  
 I. Mandić<sup>9</sup>, A. Marino<sup>19</sup>, C. Mathieu<sup>7</sup>, M. Menichelli<sup>28</sup>,  
 M. Mikuž<sup>9</sup>, A. Morozzi<sup>28</sup>, J. Moss<sup>29</sup>, R. Mountain<sup>20</sup>, A. Oh<sup>22</sup>,  
 P. Olivero<sup>15</sup>, D. Passeri<sup>28</sup>, H. Pernegger<sup>3</sup>, R. Perrino<sup>26</sup>,  
 M. Piccini<sup>28</sup>, F. Piccolo<sup>15</sup>, M. Pomorski<sup>11</sup>, R. Potenza<sup>2</sup>,  
 A. Quadri<sup>23</sup>, F. Rarbi<sup>27</sup>, A. Re<sup>15</sup>, M. Reichmann<sup>24</sup>, S. Roe<sup>3</sup>,  
 D.A. Sanz Becerra<sup>24</sup>, M. Scaringella<sup>4</sup>, C.J. Schmidt<sup>5</sup>,  
 E. Schioppa<sup>3</sup>, S. Schnetzer<sup>14</sup>, S. Sciortino<sup>4</sup>, A. Scorzoni<sup>28</sup>,  
 S. Seidel<sup>21</sup>, L. Servoli<sup>28</sup>, D.S. Smith<sup>13</sup>, B. Sopko<sup>18</sup>, V. Sopko<sup>18</sup>,  
 S. Spagnolo<sup>26</sup>, S. Spanier<sup>25</sup>, K. Stenson<sup>19</sup>, R. Stone<sup>14</sup>,  
 B. Stugo<sup>30</sup>, C. Sutura<sup>2</sup>, M. Traeger<sup>5</sup>, W. Trischuk<sup>16</sup>,  
 D. Tromson<sup>11</sup>, M. Truccato<sup>15</sup>, C. Tuve<sup>2</sup>, J. Velthuis<sup>17</sup>,  
 S. Wagner<sup>19</sup>, R. Wallny<sup>24</sup>, J.C. Wang<sup>20</sup>, J. Weingarten<sup>23</sup>,  
 C. Weiss<sup>3</sup>, N. Wermes<sup>1</sup>, M. Yamouni<sup>27</sup>, M. Zalieckas<sup>30</sup>,  
 M. Zavrtanik<sup>9</sup>

117 participants

<sup>1</sup> Universität Bonn, Bonn, Germany  
<sup>2</sup> INFN/University of Catania, Catania, Italy  
<sup>3</sup> CERN, Geneva, Switzerland  
<sup>4</sup> INFN/University of Florence, Florence, Italy  
<sup>5</sup> GSI, Darmstadt, Germany  
<sup>6</sup> Ioffe Institute, St. Petersburg, Russia  
<sup>7</sup> IPHC, Strasbourg, France  
<sup>8</sup> ITEP, Moscow, Russia  
<sup>9</sup> Jožef Stefan Institute, Ljubljana, Slovenia  
<sup>10</sup> Universität Karlsruhe, Karlsruhe, Germany  
<sup>11</sup> CEA-LIST Technologies Avances, Saclay, France  
<sup>12</sup> MEPhi Institute, Moscow, Russia  
<sup>13</sup> The Ohio State University, Columbus, OH, USA  
<sup>14</sup> Rutgers University, Piscataway, NJ, USA  
<sup>15</sup> University of Torino, Torino, Italy  
<sup>16</sup> University of Toronto, Toronto, ON, Canada  
<sup>17</sup> University of Bristol, Bristol, UK  
<sup>18</sup> Czech Technical University, Prague, Czech Republic  
<sup>19</sup> University of Colorado, Boulder, CO, USA  
<sup>20</sup> Syracuse University, Syracuse, NY, USA  
<sup>21</sup> University of New Mexico, Albuquerque, NM, USA  
<sup>22</sup> University of Manchester, Manchester, UK  
<sup>23</sup> Universität Göttingen, Göttingen, Germany  
<sup>24</sup> ETH Zürich, Zürich, Switzerland  
<sup>25</sup> University of Tennessee, Knoxville, TN, USA  
<sup>26</sup> INFN-Lecce, Lecce, Italy  
<sup>27</sup> LPSC-Grenoble, Grenoble, France  
<sup>28</sup> INFN-Perugia, Perugia, Italy  
<sup>29</sup> California State University, Sacramento, CA, USA  
<sup>30</sup> University of Bergen, Bergen, Norway

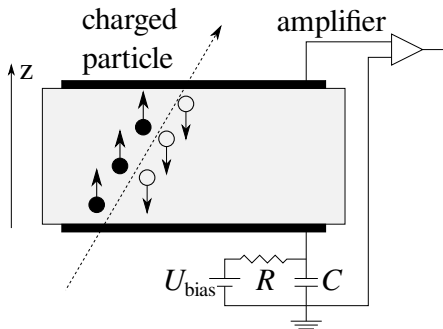
30 institutes



## Section 2

### 3D Diamond Detector

# Diamond as Particle Detector



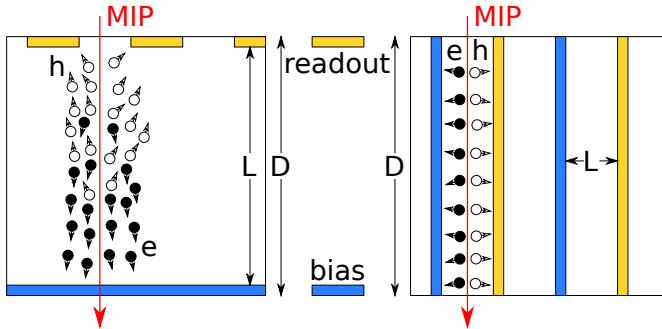
(a) Detector Schematics



(b) 15 cm  $\varnothing$  pCVD Diamond Wafer

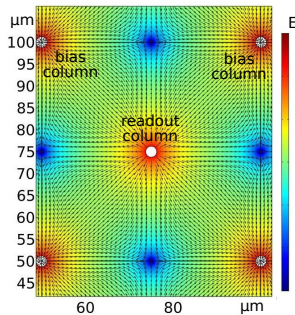
- detectors function as ionisation chambers
- metallisation on both sides
- poly-crystals produced in large wafers

# Working Principle



- after large radiation fluence all detectors become trap limited
- 3D = bias and readout electrode inside detector material
- same thickness  $D \rightarrow$  same amount of induced charge  $\rightarrow$  shorter drift distance  $L$
- **increase collected charge in detectors with limited mean drift path (Schubweg)**
- **introduce low field regions**

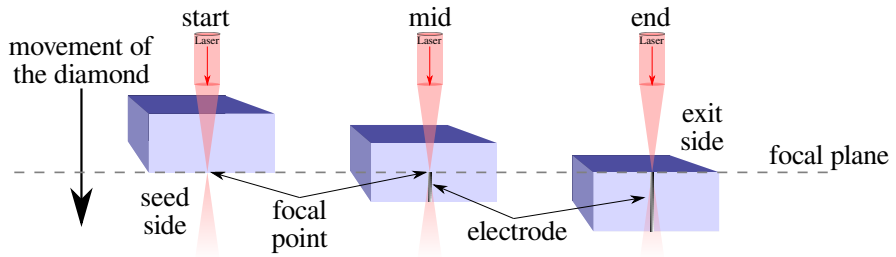
# Electric Field Simulation



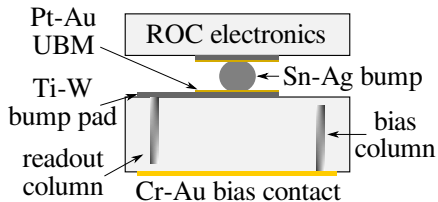
- simulation with 30 V bias voltage and periodic boundary conditions
- electric field  $\sim 1 \text{ V}/\mu\text{m}$  over a large area in the cell
- low field region in between the electrodes

# Laser drilling

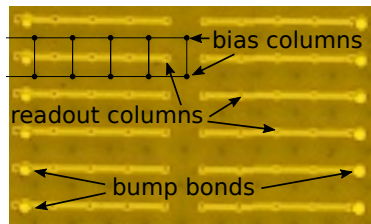
- “drilling” columns using 800 nm fs-LASER (Oxford)
- convert diamond into resistive mixture of carbon phases (i.a. DLC, graphite, ...)
- usage of Spatial Light Modulator (SLM) to correct for vertical aberration
- initial column yield  $\sim 90\%$   $\rightarrow$  now  $\geq 99.8\%$
- initial column diameter  $6 \sim 10\ \mu\text{m}$   $\rightarrow$  now  $2.6\ \mu\text{m}$



# Bump Bonding



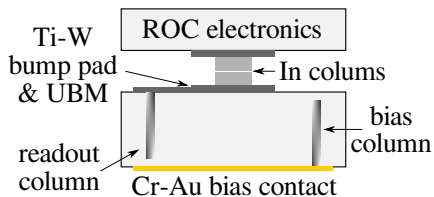
(a) Bump bond schematics



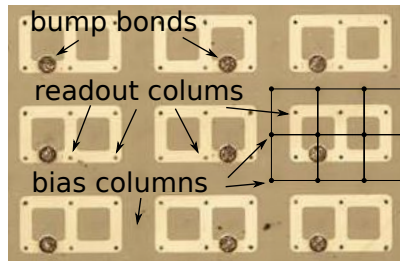
(b)  $5 \times 1$  bump pads

- connection to bias and readout with surface metallisation
- ganging of cells to match pixel pitch of readout-chip (ROC)
- small gap ( $\sim 15 \mu\text{m}$ ) to the surface

# Bump Bonding



(a) Bump bond schematics



(b)  $3 \times 2$  bump pads

- connection to bias and readout with surface metallisation
- ganging of cells to match pixel pitch of readout-chip (ROC)
- small gap ( $\sim 15 \mu\text{m}$ ) to the surface

# Progress in Diamond Detectors

## 3D Detectors - History in Diamonds:

- proved that 3D works in pCVD diamond
- scale up the number of columns per detector:  $\mathcal{O}(100) \rightarrow \mathcal{O}(1000)$  (x40)
- reducing the cell size:  $150\text{ }\mu\text{m} \times 150\text{ }\mu\text{m} \rightarrow 50\text{ }\mu\text{m} \times 50\text{ }\mu\text{m} \rightarrow 25\text{ }\mu\text{m} \times 25\text{ }\mu\text{m}$  (soon)
- reducing the diameter of the columns:  $6 \sim 10\text{ }\mu\text{m} \rightarrow 2.6\text{ }\mu\text{m} \rightarrow 1 \sim 2\text{ }\mu\text{m}$  (soon)
- $\rightarrow$  increasing column yield:  $\sim 90\% \rightarrow \geq 99.8\%$
- recently tested first irradiated  $50\text{ }\mu\text{m} \times 50\text{ }\mu\text{m}$  3D detector ( $3.5 \cdot 10^{15}\text{ n/cm}^2$ )

## 3D Pixel Detectors:

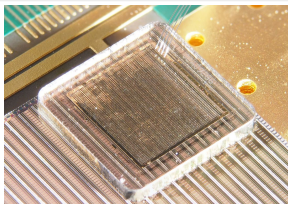
- visible improvements with each step reducing the cell size
- all worked as expected (to first order)



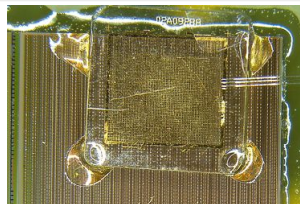
## Section 3

### Results

## Detectors



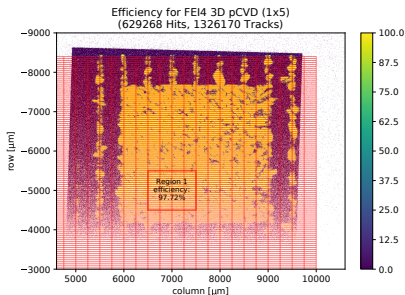
(a) B5



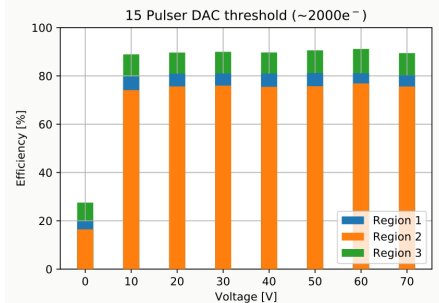
(b) B6

	B5	B6
readout chip (ROC)	FE-I4B	PSI46digv2.1respin
pixel pitch	$250\ \mu\text{m} \times 50\ \mu\text{m}$	$150\ \mu\text{m} \times 100\ \mu\text{m}$
3D cell size	$50\ \mu\text{m} \times 50\ \mu\text{m}$	$50\ \mu\text{m} \times 50\ \mu\text{m}$
ganging	$5 \times 1$	$3 \times 2$
size	$4.90\ \text{mm} \times 4.94\ \text{mm}$	$4.85\ \text{mm} \times 4.90\ \text{mm}$
thickness	$510\ \mu\text{m}$	$500\ \mu\text{m}$
50 pixels $\times$ 50 pixels	$53 \times 67$	$67 \times 53$
3D columns	7223	7223
column diameter	$2.6\ \mu\text{m}$	$2.6\ \mu\text{m}$
active area	$3.2\ \text{mm} \times 3.5\ \text{mm}$	$3.45\ \text{mm} \times 3.19\ \text{mm}$
bump bonding	tin silver (IFAE)	indium (Princeton)

## II6-B5 - Efficiencies @ CERN



(a) Efficiency map.



(b) Efficiency vs. bias voltage

- spatial resolution of  $\sim 3\mu\text{m}$
- threshold of the chip:  $\sim 1000e^-$
- efficiency in red fiducial area 97.7 %
- inefficiencies most likely due to bump bonding issues

# Time Over Threshold

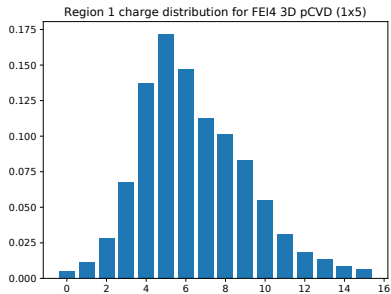
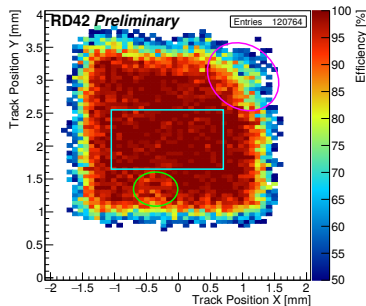


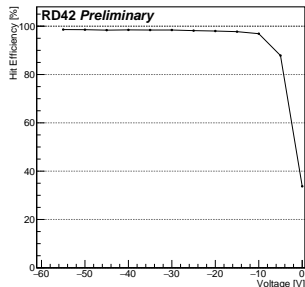
Figure: Time over threshold

- 5 tot  $\approx$  11 000 e
- mean of the ToT distribution: 6.7  $\rightarrow$   $\sim$ 15 000 e
- roughly 80 % the induced charge was collected

## I16-B6 - Efficiencies @ PSI



(a) Efficiency Map



(b) Efficiency vs. voltage.

- spatial resolution of  $\mathcal{O}(100\ \mu\text{m})$
- magenta area  $\rightarrow$  bump bonding problems, green area  $\rightarrow$  void in the diamond
- efficiency in blue box: 99.2 % ( $\rightarrow$  0.4 % due to columns)
- already fully efficient at 30 V
- ROC stopped working after this beam test

# Efficiencies @ CERN

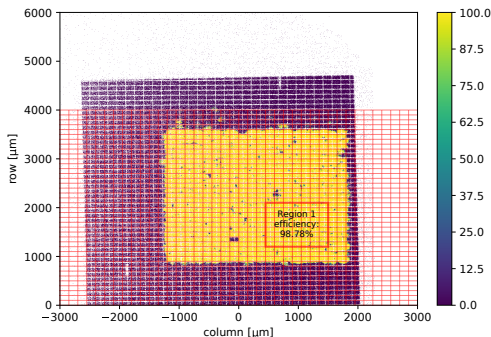


Figure: Efficiency at threshold of  $\sim 3500$  e

- high resolution measurement at CERN
- find non-working/non-connected cells
- sensor twice re-bump-bonded with the same indium (no reprocessing)
  - ▶ no removal of old bumps, no change of surface metallisation
- similar efficiency: 99.1 %

# Pulse Height @ CERN

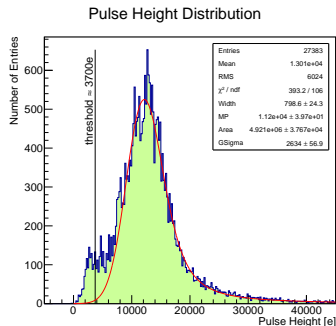


Figure: Pulse height distribution.

- threshold of the chip:  $\sim 3700$  e
- mean of the Langau fit:  $\sim 15\,000$  e
- pulse height very similar to  $5 \times 1$  result at CERN
- distribution below threshold not understood (maybe data transmission issues)

## Section 4

### Conclusion



# Conclusion

- strongly improved fabrication of 3D diamonds
  - ▶ 40 times more cells
  - ▶ smaller cell size down to  $50\text{ }\mu\text{m} \times 50\text{ }\mu\text{m}$
  - ▶ thinner columns down to  $2\text{ }\mu\text{m}$
- 3D Detectors work well in pCVD diamond
- general reasons for inefficiencies:
  - ▶ no charge created in the volume of the electrodes (0.4 % for shown devices)
  - ▶ region with low electric field
  - ▶ missing/broken columns
- 99.2 % efficiency in  $3 \times 2$  ganged device
- 97.7 % efficiency in  $5 \times 1$  ganged device
  - ▶ most likely processing issues
- consistent charge measurements for all devices:  $\sim 11\,000\text{ e}$  @ CERN SPS
- nearly full charge collection

## Section 5

### Outlook

# Outlook

- analyse  $3.5 \cdot 10^{15} \text{ n/cm}^2$  irradiated  $50 \mu\text{m} \times 50 \mu\text{m}$  detectors
- test both  $50 \mu\text{m} \times 50 \mu\text{m}$  and  $25 \mu\text{m} \times 25 \mu\text{m}$  pixel detectors
- reduce column diameter to  $1 \sim 2 \mu\text{m}$
- build pixel device on newest RD53 chip ( $50 \mu\text{m} \times 50 \mu\text{m}$  pixel pitch)
- continue scale up by 10x

# DEL FIN

